

Amendments to the Claims

Claim 1 (**Currently Amended**) A semiconductor device comprising:

- a substrate including an integrated circuit;
- an interlayer insulating layer formed on said substrate, said interlayer insulating layer having a contact hole;
- a ferroelectric capacitor formed by a first electrode layer, a ferroelectric layer and a second electrode layer deposited on said interlayer insulating layer in this order;
- a wiring layer electrically connecting said second electrode layer of said ferroelectric capacitor to said integrated circuit through said contact hole in said interlayer insulating layer; and
- an insulating side wall film covering a peripheral section of said ferroelectric capacitor and electrically insulating said peripheral section of said ferroelectric capacitor from said wiring layer, and being spaced from a peripheral edge section of said contact hole.

Claim 2 (**Previously Presented**) The semiconductor device according to the claim 1, wherein said wiring layer includes a contact plug within said contact hole.

Claim 3 (**Previously Presented**) The semiconductor device according to the claim 2, wherein said interlayer insulating layer includes a plug oxidation protective film comprising silicon nitride and silicon oxide, and said ferroelectric capacitor is mounted on said interlayer insulating layer.

Claim 4 (**Previously Presented**) The semiconductor device according to the claim 1, wherein said insulating side wall film includes a hydrogen diffusion preventing layer.

Claim 5 (**Previously Presented**) The semiconductor device according to the claim 1, wherein said ferroelectric layer comprises bismuth strontium tantalate.

Claims 6-11 (**Canceled**)

Claim 12 (**Previously Presented**) The semiconductor device according to claim 1, wherein at least a portion of said wiring layer is deposited on said insulating side wall film.

Claim 13 (**Previously Presented**) The semiconductor device according to claim 1, wherein an upper surface of said second electrode layer is free of said insulating side wall film.